

深圳市晶泰源电子有限公司

2SC5345 TRANSISTOR (NPN)

FEATURES

- RF amplifier
- High current transition frequency $f_T=550\text{MHz(Typ.)}$,
[$V_{CE}=6\text{V}$, $I_E=-1\text{mA}$]
- Low output capacitance :
 $C_{ob}=1.4\text{pF(Typ.)}$ [$V_{CB}=6\text{V}$, $I_E=0$]
- Low base time constant and high gain
- Excellent noise response

SOT-23

1. BASE
2. EMITTER
3. COLLECTOR



Marking: 5345

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	20	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current	20	mA
P_C	Collector Power dissipation	300	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}$, $I_E=0$	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=5\text{mA}$, $I_B=0$	20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}$, $I_C=0$	4			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}$, $I_E=0$			0.5	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}$, $I_C=0$			0.5	μA
DC current gain	h_{FE}	$V_{CE}=6\text{V}$, $I_C=1\text{mA}$	40		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}$, $I_B=1\text{mA}$			0.3	V
Transition frequency	f_T	$V_{CE}=6\text{V}$, $I_C=1\text{mA}$		550		MHz
Collector output capacitance	C_{ob}	$V_{CB}=6\text{V}$, $I_E=0$, $f=1\text{MHz}$		1.4		pF

CLASSIFICATION OF h_{FE}

Rank	R		
Range	100-200		